

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

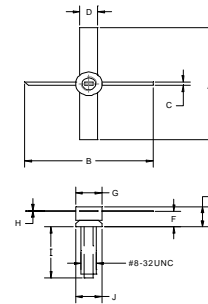
The **ASI MLN1030SS** is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	10 A
V_{CB}	60 V
V_{CE}	35 V
P_{DISS}	140 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	20 °C/W

PACKAGE STYLE .205 4L STUD


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.976 / 24.800	1.000 / 25.4000
B	.976 / 24.800	1.000 / 25.4000
C	.028 / 0.700	.031 / 0.800
D	.138 / 3.500	
E	.161 / 4.100	.196 / 5.000
F	.098 / 2.500	.110 / 2.800
G	.200 / 5.100	.208 / 5.300
H	.004 / 0.100	.006 / 0.150
I	.425 / 10.800	.465 / 11.800
J	.200 / 5.100	2.05 / 5.200

ORDER CODE: ASI10625
CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 50 mA	35			V
BV_{CER}	I _C = 50 mA R _{BE} = 10 Ω	60			V
BV_{EBO}	I _E = 10 mA	4.0			V
I_{CES}	V _E = 28 V			5.0	mA
h_{FE}	V _{CE} = 5.0 V I _C = 1.0 A	10		100	---
C_{ob}	V _{CB} = 28 V f = 1.0 MHz			5.0	pF
P_{GE}	V _{CE} = 20 V I _{CQ} = 150 mA f = 1.0 GHz P _{OUT} = 1.0 W	10			dB